





# 用于低压电源轨的单路同步降压 控制器

查询样品: TPS53015

### 特性

- D-CAP2™ 模式控制
  - 快速瞬态响应
  - 环路补偿无需外部部件
  - 与陶瓷输出电容器兼容
- 高初始参考准确度 (±1%)
- 宽输入电压范围: 4.5V 至 28V
- 输出电压范围: 0.77V 至 7.0V
- 低侧 R<sub>DS (接通)</sub> 无损电流感应
- 1.4ms 固定软启动 中将"可调软启动"改为"1.4ms 固定软启动"
- 非吸入预偏置软 启动
- 500kHz 开关频率
- 逐周期过流限制控制
- 用于在轻载时保持高效率的自动跳过 Eco-Mode<sup>TM</sup>
- 电源 良好输出

- 过流 (OCL) / 过压 (OVP) / 欠压 (UVP) / 欠压闭锁 (UVLO) / 热关断 (TSD) 保护
- 自适应栅极驱动器,带集成式升压 P 通道场效应晶体管 (PMOS) 开关
- 热补偿 OCP, 4000 ppm/°C
- 10 引脚超小型小外形尺寸封转 (VSSOP)

### 应用范围

- 针对广泛 应用的低功耗系统中的负载点调节
  - 数字电视电源
  - 网络互联家庭终端设备
  - 数字机顶盒 (STB)
  - DVD 播放器/刻录机
  - 游戏控制台和其它设备

### 说明

TPS53015 是一款单一、自使用启动时间 D-CAP2™ 模式同步降压控制器。 TPS53015 可 使系统设计人员能够通过一个成本 有效低外部组件数量和低待机电流解决方案来完成各种终端设备的电源总线调节器集。 TPS53015 的主控制环路使用 D-CAP2™ 模式控制,此控制方式 提供一个无需外部补偿组件的极快速瞬态响应。 自适应 接通时间控制支持较高负载条件下 PWM 模式与 轻负载下 Eco-mode™ 运行间的无缝转换。 Eco-mode™ 使 TPS53015 能够在较轻负载条件下保持高 效率。 TPS53015 也能够去适应诸如 POSCAP 或者 SP-CAP 的低 等效串联电阻 (ESR) 和超低 ESR 陶瓷电容器。 此器件在 4.5V 至 28V 的输入电压和 0.77V 至 7.0V 的输出电压下提供便捷和高效运行。

TPS53015 采用 3.0mm x 3.0mm 10 引脚 超小型小外形尺寸 (VSSOP) (DGS) 封装, 额定环境运行温度范围为 - 40°C 至 85°C。



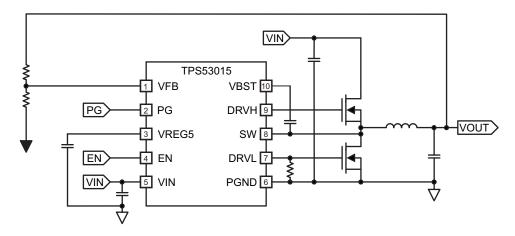
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 典型应用电路



# ORDERING INFORMATION (1)

T <sub>A</sub>	PACKAGE <sup>(1)</sup>	ORDERING PART NUMBER	PINS	OUTPUT SUPPLY	ECO PLAN
40°C to 05°C	Vecop	TPS53015DGSR	10	Tape-and-Reel	Green
–40°C to 85°C	VSSOP	TPS53015DGS	10	Tube	(RoHS & no Sb/Br)

<sup>(1)</sup> For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

## **ABSOLUTE MAXIMUM RATINGS**

Operating under free-air temperature range (unless otherwise noted) (1)

			VALUE	UNIT
		VIN, EN	-0.3 to 30	
		VBST	-0.3 to 36	
	lanut voltogo rongo	VBST - SW	-0.3 to 6	_ v
	Input voltage range	VFB	-0.3 to 6	V
		SW	-0.3 to 30	
		SW (10 nsec transient)	-3.0 to 30	
		DRVH	-2 to 36	
	Output welters are	DRVH - SW	-0.3 to 6	V
	Output voltage range	DRVL, VREG5, PG	-0.3 to 6	V
		PGND	-0.3 to 0.3	
T <sub>A</sub>	Operating ambient temp	-40 to 85	°C	
T <sub>STG</sub>	Storage temperature ra	-55 to 150	°C	
TJ	Junction temperature ra	inge	-40 to 150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



## THERMAL INFORMATION

	THERMAL METRIC <sup>(1)</sup>	TPS53015	UNITS
	I HERMAL METRIC	DGS (10 PINS)	UNITS
$\theta_{JA}$	Junction-to-ambient thermal resistance	172.2	
$\theta_{JCtop}$	Junction-to-case (top) thermal resistance	44.0	
$\theta_{JB}$	Junction-to-board thermal resistance	93.0	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.6	C/VV
ΨЈВ	Junction-to-board characterization parameter	91.4	
$\theta_{\text{JCbot}}$	Junction-to-case (bottom) thermal resistance	n/a	

<sup>(1)</sup> 有关传统和新的热 度量的更多信息,请参阅*IC 封装热度量*应用报告, SPRA953。

## **RECOMMENDED OPERATING CONDITIONS**

		MIN	MAX	UNIT
Supply input voltage range	VIN	4.5	28	V
	VBST	-0.1	33.5	
	VBST - SW	-0.1	5.5	
Input voltage range	VFB	-0.1	5.5	V
	EN	-0.1	28	
	SW	-1.0	28	
	DRVH	-1.0	33.5	
Output Valtage range	DRVH - SW	-0.1	5.5	V
Output Voltage range	DRVL, VREG5, PG	-0.1	5.5	V
	PGND	-0.1	0.1	
T <sub>A</sub> Operating free-air temperature	Operating free-air temperature		85	°C
T <sub>J</sub> Operating junction temperature	Operating junction temperature			

# **ELECTRICAL CHARACTERISTICS**

over recommended free-air temperature range, VIN = 12 V (unless otherwise noted)

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT	·	•			
I <sub>IN</sub>	VIN Supply current	urrent VIN current, $T_A = 25$ °C, $EN = 5$ V, $V_{VFB} = 0.8$ V, $V_{SW} = 0$ V		660		μA
I <sub>VINSDN</sub>	VIN Shutdown current	VIN current, $T_A = 25$ °C, No Load , $V_{EN} = 0$ V, VREG5 = OFF		6.0		μΑ
VFB VOL	TAGE and DISCHARGE RESISTA	NCE	•			
V <sub>VFBTHL</sub>	VFB Threshold voltage	T <sub>A</sub> = 25°C , V <sub>OUT</sub> = 1.05 V	765.3	773.0	780.7	mV
TC <sub>VFB</sub>	VFB Temperature coefficient	Relative to T <sub>A</sub> = 25°C <sup>(1)</sup>	-140		140	ppm/°C
I <sub>VFB</sub>	VFB Input current	VFB = 0.8V, T <sub>A</sub> = 25°C	-150	-10	100	nA
VREG5 C	DUTPUT	•	Ÿ		·	
$V_{VREG5}$	VREG5 Output voltage	$T_A=25$ °C, 6 V < $V_{IN}$ < 28 V, $I_{VREG5}$ = 5 mA		5.1		V
I <sub>VREG5</sub>	Output current	VIN = 5.5V, V <sub>VREG5</sub> = 4.0V, T <sub>A</sub> = 25°C		120		mA
OUTPUT	: N-CHANNEL MOSFET GATE DRI	VERS				
D	DRVH resistance	Source, I <sub>DRVH</sub> = -50mA, T <sub>A</sub> = 25°C		3.2	4.7	Ω
$R_{DRVH}$	DRVH resistance	Sink, $I_{DRVH} = 50mA$ , $T_A = 25$ °C		1.4	2.4	12
D	DDV//i-ton	Source, I <sub>DRVL</sub> = -50mA, T <sub>A</sub> = 25°C		6.9	8.2	Ω
$R_{DRVL}$	DRVL resistance	Sink, I <sub>DRVL</sub> = 50mA, T <sub>A</sub> = 25°C	0.8 1.			12
	Dead time	DRVH-low to DRVL-on <sup>(1)</sup>		15		20
$T_D$	Deau lime	DRVL-low to DRVH-on <sup>(1)</sup>		20		ns

<sup>(1)</sup> Ensured by design. Not production tested.



over recommended free-air temperature range, VIN = 12 V (unless otherwise noted)

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
INTERNAL	BOOST DIODE		·			
V <sub>FBST</sub>	Forward voltage	V <sub>VREG5-VBST</sub> , I <sub>F</sub> = 10mA, T <sub>A</sub> = 25°C		0.1	0.2	V
SOFT STAF	<b>R</b> T					
T <sub>ss</sub>	Internal soft start time			1.4		ms
POWER GO	OOD					-
$V_{PGTH}$	PGOOD threshold	PGOOD LOW		84		%
		PGOOD HIGH		116		%
I <sub>PG</sub>	PGOOD sink current	V <sub>PG</sub> = 0.5 V		5		mA
_	PGOOD delay time	Delay for PGOOD in		1.2		ms
T <sub>PGDLY</sub>		Delay for PGOOD out		2		μs
T <sub>PGCOMPSS</sub>	PGODD comparator start up delay	PGOOD comparator wake up delay		2.3		ms
UVLO			<del></del>			
	VDECE IIVI O threehold	VREG5 Rising		4.0		V
$V_{UVVREG5}$	VREG5 UVLO threshold	Hysteresis		0.3		
LOGIC THE	RESHOLD		·			
V <sub>ENH</sub>	EN H-level threshold voltage		1.6			V
V <sub>ENL</sub>	EN L-level threshold voltage				0.5	V
R <sub>EN</sub>	EN pin resistance to GND	V <sub>EN</sub> = 12 V	225	450	900	kΩ
CURRENT	SENSE		·			
I <sub>TRIP</sub>	TRIP Source current	$V_{DRVL} = 0.1V, T_A = 25^{\circ}C$	14.3	15	15.8	μA
TC <sub>VTRIP</sub>	V <sub>TRIP</sub> Temperature coefficient	Relative to T <sub>A</sub> = 25°C		4000		ppm/°C
		$R_{TRIP} = 75k\Omega$ , $T_A = 25^{\circ}C$	234	336	424	
$V_{OCL}$	Current limit threshold	$R_{TRIP} = 27k\Omega$ , $T_A = 25^{\circ}C$	121	174	220	mV
		$R_{TRIP} = 6.8k\Omega$ , $T_A = 25^{\circ}C$	35	50	63	
ON-TIME T	IMER CONTROL					
T <sub>ON</sub>	On time	$V_{OUT} = 1.05 V^{(2)}$		250		ns
$T_{OFF(MIN)}$	Minimum off time	$V_{IN} = 4.5 \text{ V}, V_{VFB} = 0.7 \text{ V}, T_A = 25^{\circ}\text{C}$		230		ns
OUTPUT U	NDERVOLTAGE AND OVERVOLTA	GE PROTECTION				
V <sub>OVP</sub>	Output OVP trip threshold	OVP detect voltage	115	120	125	%
T <sub>OVPDEL</sub>	Output OVP propagation delay				10	μs
$V_{UVP}$	Output UVP trip threshold	UVP detect voltage	63	68	73	%
T <sub>UVPDEL</sub>	Output UVP delay			1		ms
T <sub>UVPEN</sub>	Output UVP enable delay		1.7	2.2	2.7	ms
THERMAL	SHUTDOWN					
T	Thormal chutdows throshold	Shutdown temperature (2)		150		°C
T <sub>SDN</sub>	Thermal shutdown threshold	Hysteresis <sup>(2)</sup>	25			7

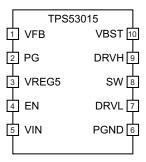
<sup>(2)</sup> Ensured by design. Not production tested.



## **PIN FUNCTIONS**

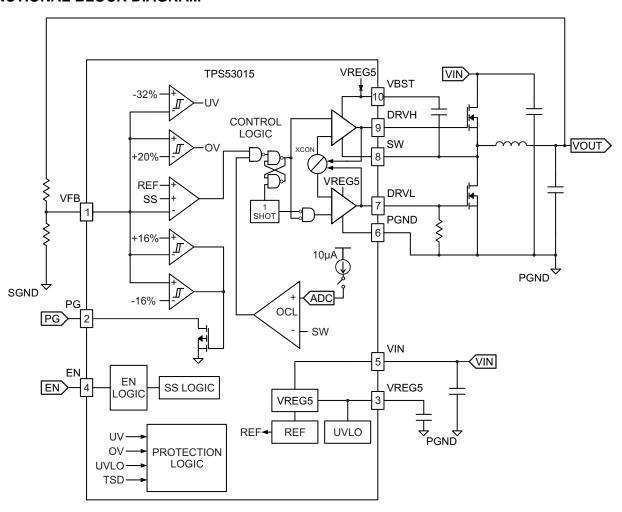
PIN		I/O	DESCRIPTION
NAME	VSSOP-10		
VFB	1	I	D-CAP2 feedback input. Connect to output voltage with resistor divider.
PG	2	0	Open drain power good output.
VREG5	3	0	Output of 5-V linear regulator and supply for MOSFET driver. Bypass to GND with a minimum 4.7-µF high quality ceramic capacitor. VREG5 is active when EN is asserted high.
EN	4	ı	Enable. Pull High to enable converter.
VIN	5	ı	Supply Input for 5-V linear regulator. Bypass to GND with a minimum 0.1-µF high quality ceramic capacitor.
PGND	6	I	System ground.
DRVL	7	0	Low-side N-Channel MOSFET gate driver output. PGND referenced driver switches between PGND(OFF) and VREG5(ON).
SW	8	I/O	Switch node connections for both the high-side driver and over current comparator.
DRVH	9	0	High-side N-channel MOSFET gate driver output. SW referenced driver switches between SW(OFF) and VBST(ON).
VBST	10	I	High-side MOSFET gate driver bootstrap voltage input. Connect a capacitor from VBST to SW. An internal diode is connected between VREG5 and VBST

# 10 PIN VSSOP (TOP VIEW)





### **FUNCTIONAL BLOCK DIAGRAM**



### **OVERVIEW**

The TPS53015 is single synchronous step-down (buck) controller. It operates using D-CAP2™ mode control. The fast transient response of D-CAP2™ control reduces the required amount of output capacitance to meet a specific level of performance. Proprietary internal circuitry allows the use of low ESR output capacitors including ceramic and special polymer types.

### **DETAILED DESCRIPTION**

### **PWM OPERATION**

The main control loop of the TPS53015 is an adaptive on-time pulse width modulation (PWM) controller that supports a proprietary D-CAP2™ control mode. D-CAP2™ control combines constant on-time control with an internal compensation circuit for pseudo-fixed frequency and low external component count configuration with both low ESR and ceramic output capacitors. It is stable even with virtually no ripple at the output. At the beginning of each cycle, the high-side MOSFET is turned on. this MOSFET is turned off when the internal timer expires. This timer is set by the converter input voltage VIN, and the output voltage VO, to maintain a pseudo-fixed frequency over the input voltage range, hence it is called adaptive on-time control. The timer is reset and the high-side MOSFET is turned on again when the feedback voltage falls below the nominal output voltage. An internal ramp is added to the reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP2™ mode control.



### **AUTO-SKIP Eco-Mode™ CONTROL**

The TPS53015 is designed with Auto-Skip Eco-mode™ to increase light load efficiency. As the output current decreases from heavy load condition, the inductor current is also reduced and eventually comes to point where its rippled valley touches zero level, which is the boundary between continuous conduction and discontinuous conduction modes. The rectifying MOSFET is turned off when its zero inductor current is detected. As the load current further decreases the converter run into discontinuous conduction mode. The on-time is kept almost half as is was in the continuous conduction mode because it takes longer time to discharge the output capacitor with smaller load current to the level of the reference voltage. The transition point to the light load operation IOX(LL) current can be calculated in Equation 1 with 500kHz used as fsw.

$$I_{OUT(LL)} = \frac{1}{2 \times L \times f_{SW}} \times \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN}}$$
(1)

### **DRIVERS**

TPS53015 contains two high-current resistive MOSFET gate drivers. The low-side driver is a PGND referenced, VREG5 powered driver designed to drive the gate of a high-current, low  $R_{DS(on)}$  N-channel MOSFET whose source is connected to PGND. The high-side driver is a floating SW referenced, VBST powered driver designed to drive the gate of a high-current, low  $R_{DS(on)}$  N-channel MOSFET. To maintain the VBST voltage during the high-side driver ON time, a capacitor is placed from SW to VBST. Each driver draws average current equal to Gate Charge ( $Q_g @ V_{gs} = 5V$ ) times Switching frequency (fsw). To prevent cross-conduction, there is a narrow dead-time when both high-side and low-side drivers are OFF between each driver transition. During this time the inductor current is carried by one of the MOSFETs body diodes.

#### 5-VOLT REGULATOR

The TPS53015 has an internal 5V Low-Dropout (LDO) Regulator to provide a regulated voltage for all both drivers and the ICs internal logic. A high-quality 4.7μF or greater ceramic capacitor from VREG5 to GND is required to stabilize the internal regulator.

### SOFT START AND PRE-BIASED SOFT START

The TPS53015 has an internally set, 1.4 ms soft start time. When the EN pin becomes high and the VREG5 voltage is above the UVLO threshold, an internal DAC ramps up the reference voltage to the PWM comparator. Smooth control of the output voltage is maintained during start up.

The TPS53015 contains a unique circuit to prevent current from being pulled from the output during startup if the output is pre-biased. When the soft-start commands a voltage higher than the pre-bias level (internal soft start becomes greater than internal feedback voltage VFB), the controller slowly activates synchronous rectification by starting the first low side FET gate driver pulses with a narrow on-time. It then increments that on-time on a cycle-by-cycle basis until it coincides with the time dictated by (1-D), where D is the duty cycle of the converter. This scheme prevents the initial sinking of the pre-biased output, and ensures that the output voltage (VO) starts and ramps up smoothly into regulation from pre-biased startup to normal mode operation.



### **OVER CURRENT PROTECTION**

TPS53015 has a cycle-by-cycle over current limit feature. The over current limits the inductor valley current by monitoring the voltage drop across the low-side MOSFET  $R_{DS(on)}$  during the low-side driver on-time. If the inductor current is larger than the over current limit (OCL), the TPS53015 delays the start of the next switching cycle until the sensed inductor current falls below the OCL current. MOSFET  $R_{DS(on)}$  current sensing is used to provide an accuracy and cost effective solution without external devices. To program the OCL, a resister should be connected between DRVL and PGND. The recommended values are given in Table 1.

**Table 1. OCL Resistor Values** 

Resister Value ( kΩ)	V <sub>trip</sub> (V)
6.8	0.050
11	0.087
18	0.125
27	0.174
39	0.224
56	0.274
75	0.336

I<sub>OCL</sub> is determined by Equation 2.

$$I_{OCL} = \left(\frac{\left(V_{IN} - V_{OUT}\right)}{2 \times L \times f_{SW}} \times \frac{V_{OUT}}{V_{IN}}\right) + \frac{V_{TRIP}}{R_{DS(ON)}}$$

(2)

The trip voltage is set between 0.05V to 0.336V over all operational temperature, including the  $4000ppm/^{\circ}C$  temperature slope compensation for the temperature dependency of the  $R_{DS(on)}$ . If the load current exceeds the over-current limit, the voltage will begin to drop. If the over-current conditions continues the output voltage will fall below the under voltage protection threshold and the TPS53015 will shut down.

#### **OVER/UNDER VOLTAGE PROTECTION**

TPS53015 monitors a resistor divided feedback voltage to detect over and under voltage. If the feedback voltage is higher than 120% of the reference voltage, the OVP comparator output goes high and the circuit latches the high-side MOSFET driver OFF and the low-side MOSFET driver ON.

When the feedback voltage is lower than 68% of the reference voltage, the UVP comparator output goes high and an internal UVP delay counter begins counting. After 1ms, TPS53015 latches OFF both top and bottom MOSFET drivers. This function is enabled approximately 2.2 ms after power-on. The OVP and UVP latch off is reset when EN goes low.

#### **UVLO PROTECTION**

TPS53015 has under voltage lock out protection (UVLO) that monitors the voltage of VREG5 pin. When the VREG5 voltage is lower than UVLO threshold voltage, the device is shut off. All output drivers are OFF. The UVLO is non-latch protection.

### THERMAL SHUTDOWN

TPS53015 monitors its temperature. If the temperature exceeds the threshold value (typically 150°C), the device shuts off. When the temperature falls below the threshold, the IC starts again. When VIN starts up and VREG5 output voltage is below its nominal value, the thermal shutdown threshold is kept lower than 150°C. As long as VIN rises, T<sub>J</sub> must be kept less than 110°C.

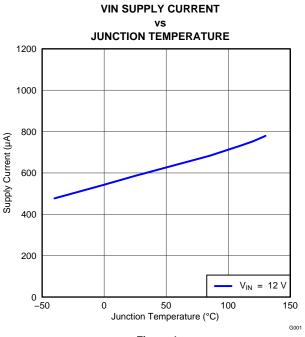
#### **POWER GOOD**

The TPS53015 has a power-good output that this is measured on VFB. The power-good function is activated after soft-start has finished. If the output voltage is within  $\pm 16\%$  of the target voltage, the internal comparator detects the power-good state and the power-good signal becomes high after 1.2ms delay. During start-up, this internal delay starts after 2.2 times the soft-start time to avoid a glitch of power-good signal. If the feedback voltage goes outside  $\pm 16\%$  of target value, the power-good signal becomes low after  $2\mu$ s delay.

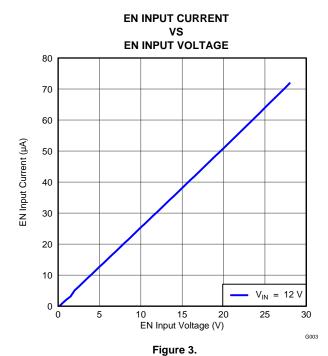


### **TYPICAL CHARACTERISTICS**

 $V_{IN}$  = 12 V,  $T_A$ = 25 °C (unless otherwise noted)



#### Figure 1.



VIN SHUTDOWN CURRENT

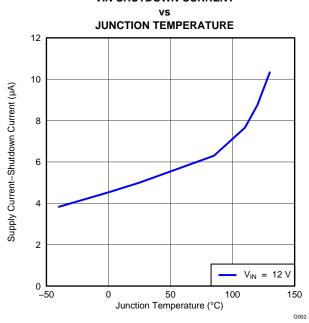


Figure 2.

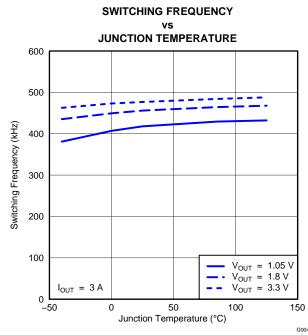
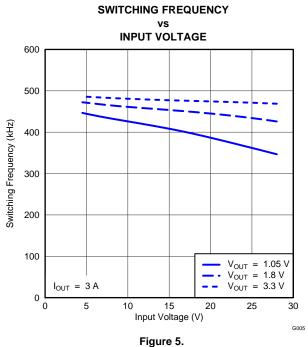
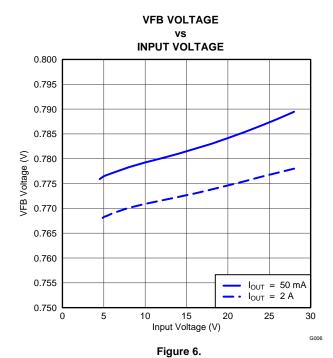


Figure 4.

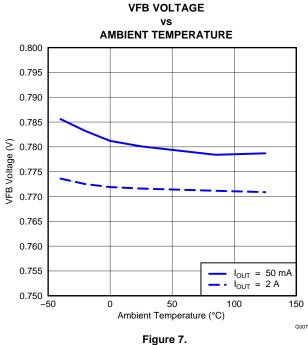


 $V_{IN}$  = 12 V,  $T_A$ = 25 °C (unless otherwise noted)









**LOAD REGULATION** 1.10 1.09 1.08 1.07 Output Voltage (V) 1.06 1.05 1.04 1.03 1.02  $V_{IN} = 5 V$   $V_{IN} = 12 V$ 1.01  $V_{IN} = 28 \text{ V}$ 1.00 1.0 2.0 3.0 4.0 5.0 6.0 7.0 8.0 Output Current (A) G008

Figure 8.



 $V_{IN} = 12 \text{ V}, T_A = 25 \text{ °C (unless otherwise noted)}$ 

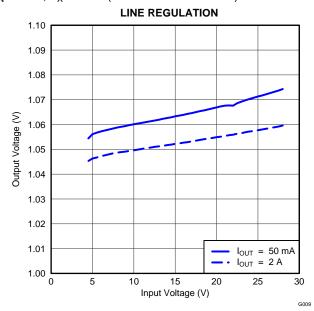


Figure 9.

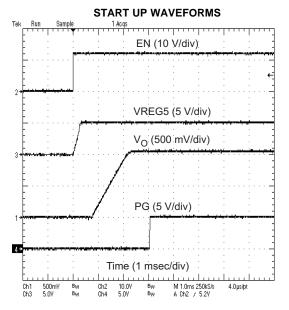


Figure 11.

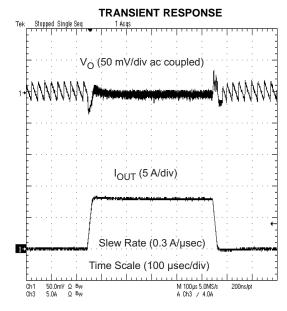


Figure 10.

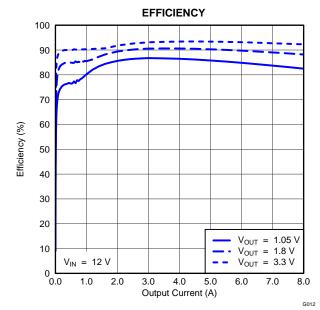


Figure 12.



 $V_{IN}$  = 12 V,  $T_A$ = 25 °C (unless otherwise noted)

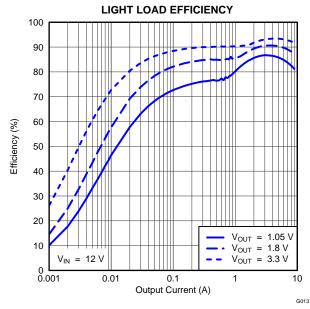


Figure 13.

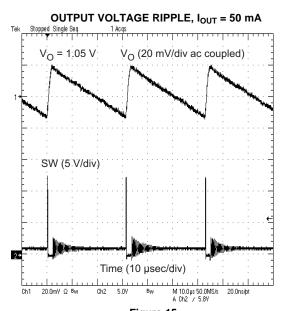


Figure 15.

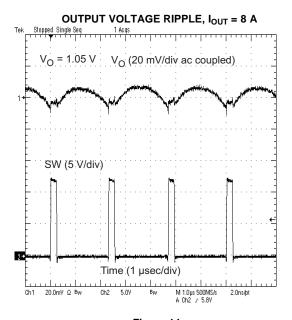


Figure 14.

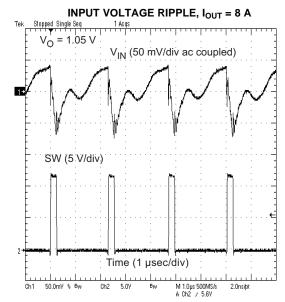


Figure 16.



 $V_{IN}$  = 12 V,  $T_A$ = 25 °C (unless otherwise noted)

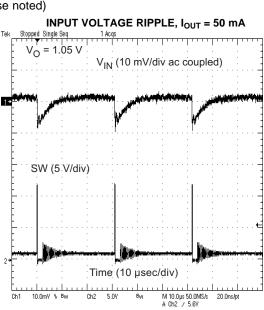


Figure 17.



#### APPLICATION INFORMATION

### **APPLICATION SCHEMATIC**

A typical application schematic is shown in Figure 18.

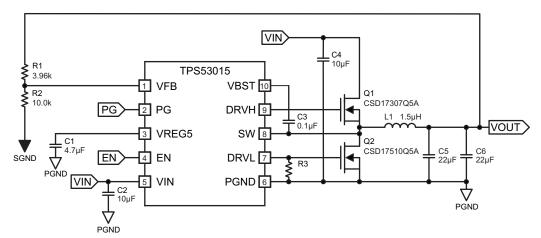


Figure 18. Application Schematic

### **COMPONENT SELECTION**

### **INDUCTOR**

The inductance value is selected to provide approximately 30% peak to peak ripple current at maximum load. Larger ripple current increases output ripple voltage, improve S/N ratio and contribute to stable operation. Equation 3 can be used to calculate te value for  $L_{OUT}$ .

$$L_{OUT} = \frac{V_{IN(MAX)} - V_{OUT}}{I_{L(RIPPLE)} \times f_{SW}} \times \frac{V_{OUT}}{V_{IN(MAX)}}$$
(3)

The inductors current ratings needs to support both the RMS (thermal) current and the peak (saturation) current. The RMS and peak inductor current can be estimated as follows:

$$I_{L(RIPPLE)} = \frac{V_{IN(MAX)} - V_{OUT}}{L_{OUT} \times f_{SW}} \times \frac{V_{OUT}}{V_{IN(MAX)}}$$
(4)

$$I_{L(PEAK)} = \frac{V_{TRIP}}{R_{DS(ON)}} + I_{L(RIPPLE)}$$
(5)

$$I_{L(RMS)} = \sqrt{I_{OUT}^2 + \frac{1}{12} \times I_{L(RIPPLE)}^2}$$
(6)

Note:

The calculation above shall serve as a general reference. To further improve transient response, the output inductance could be reduced further. This needs to be considered along with the selection of the output capacitor.

### **OUTPUT CAPACITOR**

The capacitor value and ESR determines the amount of output voltage ripple and load transient response. Ceramic output capacitors with X5R dielectric or better are recommended.

$$C_{OUT} = \frac{I_{L(RIPPLE)}}{8 \times V_{OUT(RIPPLE)}} \times \frac{1}{f_{SW}}$$
(7)



$$C_{OUT} = \frac{\Delta I_{LOAD}^2}{2 \times V_{OUT} \times \Delta V_{OS}} \times L_{OUT}$$
(8)

$$C_{OUT} = \frac{\Delta I_{LOAD}^2}{2 \times K \times \Delta V_{US}} \times L_{OUT}$$
(9)

Where:

$$K = (V_{IN} - V_{OUT}) \times \frac{T_{ON}}{T_{ON} - T_{OFF(MIN)}}$$
(10)

- ΔV<sub>OS</sub> = The allowable amount of overshoot voltage in load transition
- ΔV<sub>US</sub> = The allowable amount of undershoot voltage in load transition
- T<sub>OFF(MIN)</sub> = Minimum off time

Select the capacitance value greater than the largest value calculated from Equation 7, Equation 8 and Equation 9. The minimum recommended output capacitance is  $44 \mu F$ .

### **INPUT CAPACITOR**

The TPS53015 requires an input decoupling capacitor and a bulk capacitor is needed depending on the application. A minimum 10-µF high-quality ceramic capacitor is recommended for the input capacitor. The capacitor voltage rating needs to be greater than the maximum input voltage.

#### **BOOTSTRAP CAPACITOR**

The TPS53015 requires a bootstrap capacitor from SW to VBST to provide the floating supply for the high-side drivers. A minimum 0.1-µF high-quality ceramic capacitor is recommended. The capacitor voltage rating should be greater than 10 V.

### **VREG5 CAPACITOR**

The TPS53015 requires that the VREG5 regulator is bypassed. A minimum 4.7-µF high-quality ceramic capacitor must be connected between the VREG5 and PGND for proper operation. The capacitor voltage rating should be greater than 10 V.

### **CHOOSE OUTPUT VOLTAGE RESISTORS**

The output voltage is set with a resistor divider from output voltage node to the VFB pin. It is recommended to use 1% tolerance or better resistors. Select R2 between 10 k $\Omega$  and 100 k $\Omega$  and use Equation 11 to calculate R1.

$$R1 = \left(\frac{V_{OUT}}{V_{VFB}} - 1\right) \times R2 \tag{11}$$

### LAYOUT SUGGESTIONS

- Keep the input switching current loop as small as possible.
- Place the input capacitor close to the top switching FET. The output current loop should also be kept as small as possible.
- Keep the SW node as physically small and short as possible as to minimize parasitic capacitance and inductance and to minimize radiated emissions. Kelvin connections should be brought from the output to the feedback pin (VFB) of the device.
- Keep analog and non-switching components away from switching components.
- Make a single point connection from the signal ground to power ground.
- Do not allow switching current to flow under the device.



# **REVISION HISTORY**

Cł	nanges from Original (July 2012) to Revision A	age
•	Added 将版本 A 添加到文献编号	1
•	Changed Package designator from DDA to DGS in Thermal Information table header	3
Cł	nanges from Revision A (July 2012) to Revision B	age
•	Changed 文献编号从修订版本 A 改为修订版本 B	1
•	Changed 在 特性列表	1
•	Added 将"电源 良好输出"添加到特性	1
•	Changed from "SS" to "PG" in the Absolute Maximum Ratings table	2
•	Changed from "SS" to "PG" in the Recommended Operating Conditions table	3
•	Changed T <sub>SS</sub> spec from "1.0 ms" to "1.4 ms" Typical	4
•	Changed T <sub>PGDLY</sub> spec from "1.5 ms" to "1.2 ms"	
•	Changed T <sub>PGCOMPSS</sub> spec from "2.2 ms" to "2.3 ms"	
•	Changed T <sub>UVPEN</sub> spec from "1.4 ms, 1.7 ms, 2.0 ms" MIN, TYP, MAX to "1.7 ms, 2.2 ms, 2.7 ms" respectively	
•	Changed "+10%" and "-10%" to "+16%" and "-16%" in the Functional Block Diagram	6
•	Changed soft start time from "1.0 ms" to "1.4 ms"	7
•	Changed timing from "1.7 ms" to "2.2 ms" in the OVER/UNDER VOLTAGE PROTECTION section	8
•	Added section describing POWER GOOD operation	8



# PACKAGE OPTION ADDENDUM

11-Apr-2013

### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
TPS53015DGS	ACTIVE	VSSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	53015	Samples
TPS53015DGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 85	53015	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

# PACKAGE MATERIALS INFORMATION

www.ti.com 19-Nov-2012

# TAPE AND REEL INFORMATION





		Dimension designed to accommodate the component width
E	30	Dimension designed to accommodate the component length
K	(0	Dimension designed to accommodate the component thickness
	N	Overall width of the carrier tape
F	21	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS53015DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

**PACKAGE MATERIALS INFORMATION** 

www.ti.com 19-Nov-2012

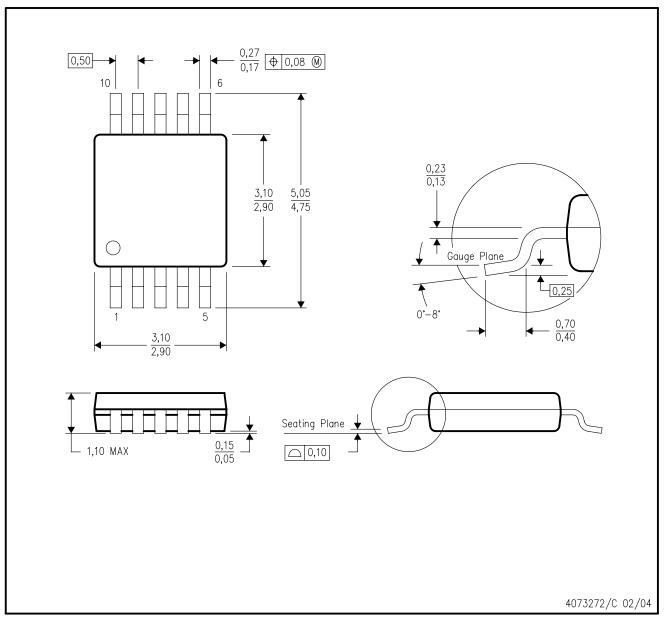


### \*All dimensions are nominal

ĺ	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
	TPS53015DGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0

# DGS (S-PDSO-G10)

# PLASTIC SMALL-OUTLINE PACKAGE



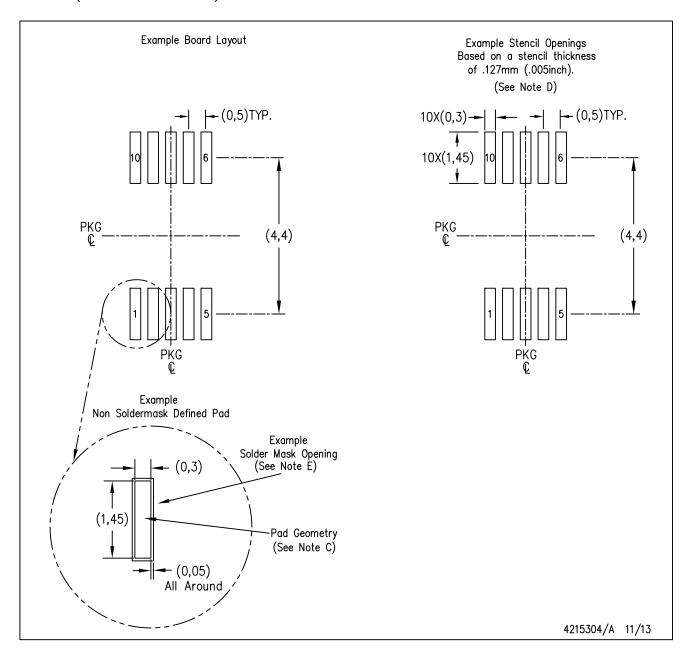
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.



# DGS (S-PDSO-G10)

# PLASTIC SMALL OUTLINE PACKAGE



### NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



### 重要声明

德州仪器(TI) 及其下属子公司有权根据 JESD46 最新标准, 对所提供的产品和服务进行更正、修改、增强、改进或其它更改, 并有权根据 JESD48 最新标准中止提供任何产品和服务。客户在下订单前应获取最新的相关信息, 并验证这些信息是否完整且是最新的。所有产品的销售都遵循在订单确认时所提供的TI 销售条款与条件。

TI 保证其所销售的组件的性能符合产品销售时 TI 半导体产品销售条件与条款的适用规范。仅在 TI 保证的范围内,且 TI 认为 有必要时才会使用测试或其它质量控制技术。除非适用法律做出了硬性规定,否则没有必要对每种组件的所有参数进行测试。

TI 对应用帮助或客户产品设计不承担任何义务。客户应对其使用 TI 组件的产品和应用自行负责。为尽量减小与客户产品和应 用相关的风险,客户应提供充分的设计与操作安全措施。

TI 不对任何 TI 专利权、版权、屏蔽作品权或其它与使用了 TI 组件或服务的组合设备、机器或流程相关的 TI 知识产权中授予 的直接或隐含权限作出任何保证或解释。TI 所发布的与第三方产品或服务有关的信息,不能构成从 TI 获得使用这些产品或服 务的许可、授权、或认可。使用此类信息可能需要获得第三方的专利权或其它知识产权方面的许可,或是 TI 的专利权或其它 知识产权方面的许可。

对于 TI 的产品手册或数据表中 TI 信息的重要部分,仅在没有对内容进行任何篡改且带有相关授权、条件、限制和声明的情况 下才允许进行 复制。TI 对此类篡改过的文件不承担任何责任或义务。复制第三方的信息可能需要服从额外的限制条件。

在转售 TI 组件或服务时,如果对该组件或服务参数的陈述与 TI 标明的参数相比存在差异或虚假成分,则会失去相关 TI 组件 或服务的所有明示或暗示授权,且这是不正当的、欺诈性商业行为。TI 对任何此类虚假陈述均不承担任何责任或义务。

客户认可并同意,尽管任何应用相关信息或支持仍可能由 TI 提供,但他们将独力负责满足与其产品及在其应用中使用 TI 产品 相关的所有法律、法规和安全相关要求。客户声明并同意,他们具备制定与实施安全措施所需的全部专业技术和知识,可预见 故障的危险后果、监测故障及其后果、降低有可能造成人身伤害的故障的发生机率并采取适当的补救措施。客户将全额赔偿因 在此类安全关键应用中使用任何 TI 组件而对 TI 及其代理造成的任何损失。

在某些场合中,为了推进安全相关应用有可能对 TI 组件进行特别的促销。TI 的目标是利用此类组件帮助客户设计和创立其特 有的可满足适用的功能安全性标准和要求的终端产品解决方案。尽管如此,此类组件仍然服从这些条款。

TI 组件未获得用于 FDA Class III (或类似的生命攸关医疗设备)的授权许可,除非各方授权官员已经达成了专门管控此类使用的特别协议。

只有那些 TI 特别注明属于军用等级或"增强型塑料"的 TI 组件才是设计或专门用于军事/航空应用或环境的。购买者认可并同 意,对并非指定面向军事或航空航天用途的 TI 组件进行军事或航空航天方面的应用,其风险由客户单独承担,并且由客户独 力负责满足与此类使用相关的所有法律和法规要求。

TI 己明确指定符合 ISO/TS16949 要求的产品,这些产品主要用于汽车。在任何情况下,因使用非指定产品而无法达到 ISO/TS16949 要求,TI不承担任何责任。

	产品		应用	
数字音频	www.ti.com.cn/audio	通信与电信	www.ti.com.cn/telecom	
放大器和线性器件	www.ti.com.cn/amplifiers	计算机及周边	www.ti.com.cn/computer	
数据转换器	www.ti.com.cn/dataconverters	消费电子	www.ti.com/consumer-apps	
DLP® 产品	www.dlp.com	能源	www.ti.com/energy	
DSP - 数字信号处理器	www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial	
时钟和计时器	www.ti.com.cn/clockandtimers	医疗电子	www.ti.com.cn/medical	
接口	www.ti.com.cn/interface	安防应用	www.ti.com.cn/security	
逻辑	www.ti.com.cn/logic	汽车电子	www.ti.com.cn/automotive	
电源管理	www.ti.com.cn/power	视频和影像	www.ti.com.cn/video	
微控制器 (MCU)	www.ti.com.cn/microcontrollers			
RFID 系统	www.ti.com.cn/rfidsys			
OMAP应用处理器	www.ti.com/omap			
无线连通性	www.ti.com.cn/wirelessconnectivity	德州仪器在线技术支持社区	www.deyisupport.com	

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2016, Texas Instruments Incorporated